

**Semiconductor Device Modelling and Simulation**  
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**Lecture – 43**  
**Drift Diffusion Model (Continued)**

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The slide features a blue header with the text "L43 SCALING AND DISCRETIZATION" and the IIT Kharagpur logo on the left and right. Below the header, there is a list of two bullet points: "Scaling and Linearization of Poisson's Equation" and "Scharfetter-Gummel Discretization of the Continuity Equation". The second bullet point is underlined. In the bottom right corner, there is a small video inset showing Prof. Vivek Dixit speaking. At the bottom of the slide, there is a purple bar with the text "SEMICONDUCTOR DEVICE MODELING AND SIMULATION".

Hello, welcome to lecture number 43. So, in this lecture we will discuss about the scaling and the discretization method for drift diffusion model. In the discretizing this Scharfetter Gummel discretization is very important because that ensures that when you do the simulation it actually converges. And we will also discuss the problem with normal discretization of the continuity equation.

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DRIFT DIFFUSION MODEL

<p><b>Charge density and Poisson equation</b></p> $\rho = q(p - n + N_D^+ - N_A^-)$ $\frac{d\bar{E}}{dx} = \frac{\rho}{\epsilon}; \frac{d\psi}{dx} = -E; \frac{dE_x}{dx} = q\bar{E}$	<p><b>Carrier density equations</b></p> $n = n_i \exp\left(\frac{q(\psi - \phi_i)}{k_B T}\right)$ $p = n_i \exp\left(\frac{q(\phi_i - \psi)}{k_B T}\right)$	<p><b>current density equations</b></p> $\bar{J}_n = qn\mu_n \bar{E} + qD_n \frac{dn}{dx}$ $\bar{J}_p = qp\mu_p \bar{E} - qD_p \frac{dp}{dx}$
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**Continuity equations with SRH recombination**

$$\frac{dn}{dt} = \frac{1}{q} \frac{dJ_n}{dx} - \frac{np - n_i^2}{n + p + 2n_i \cosh\left(\frac{E_i - E_f}{k_B T}\right)} \frac{1}{\tau} + G - R$$

$$\frac{dp}{dt} = -\frac{1}{q} \frac{dJ_p}{dx} - \frac{np - n_i^2}{n + p + 2n_i \cosh\left(\frac{E_i - E_f}{k_B T}\right)} \frac{1}{\tau} + G - R$$

$\frac{\partial \psi}{\partial x} = -E = -\frac{q}{\epsilon} (p - n + N_D^+ - N_A^-)$

$= -\frac{q}{\epsilon} (p - n + c)$

SEMICONDUCTOR DEVICE MODELING AND SIMULATION

Now, let us recall the drift diffusion model, so, there is a charge density and the Poisson equation. So, generally, the poisson equation is written like this  $\frac{d^2 \psi}{dx^2} = \frac{\rho}{\epsilon}$ . So, here,  $\psi$  of potential is equal to minus rho by epsilon times  $p - n + N_D^+ - N_A^-$ . Now, these are fixed charge, so, they can return as  $c$ . So, this is  $-\rho$  by epsilon times  $p - n + \text{some } C$ . And  $n$  can be written as  $n_i \exp\left(\frac{q(\psi - \phi_i)}{k_B T}\right)$ .

So, this is related to Fermi potential, so, here it should be actually  $\psi$ . Then your  $n$  is written as basically,  $n_i \exp\left(\frac{q(\psi - \phi_i)}{k_B T}\right)$ . Now, the difference between this potential  $\psi$  and  $\phi_i$  or you can write  $E_F - E_i$  is actually  $q$  times  $V$  the potency difference potential applied potential  $V$ . Because with respect to the applied potential the Fermi potential follows applied potential with respect to the internal potential.

So, the difference is basically the applied voltage. Then you have this current density equation where you have a drift current plus diffusion current. And then of course, the continuity equation. So, this is written for SRH but you can write a general expression which is  $+G - R$  or  $+G - R$  where  $G$  is the generation rate and  $R$  is the recombination rate. Because generation rate tend to increase the carriers, so, it is plus recombination tend to decrease it, so, it is minus.

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**LINEARIZATION OF POISSON EQUATION**

Poisson equation

$$\frac{d^2\psi}{dx^2} = -\frac{\rho}{\epsilon} = -\frac{q}{\epsilon}(p - n + N_D^+ - N_A^-)$$

Carrier density equations

$$n = n_i \exp\left(\frac{E_F - E_i}{k_B T}\right) = n_i \exp\left(\frac{q(\psi - \phi_n)}{k_B T}\right) = n_i \exp\left(\frac{V}{V_T}\right)$$

$$p = n_i \exp\left(\frac{E_i - E_F}{k_B T}\right) = n_i \exp\left(\frac{q(\phi_p - \psi)}{k_B T}\right) = n_i \exp\left(-\frac{V}{V_T}\right)$$

$\psi_p = -q\phi_n$   
 $\psi_n = q\phi_p$

SEMICONDUCTOR DEVICE MODELING AND SIMULATION

Now, linearization of the Poisson equation. So, this is  $d^2 \psi$  by  $dx^2$  is equal to minus  $\rho$  by  $\epsilon$ . So, this is  $-q$  by  $p - n + N_D^+ - N_A^-$  by this is the equation. And then the carrier density equation you have seen different forms  $E_F - E_i$  by  $kT$  then that is also written as  $q\psi - \phi_n$  by  $kT$  where  $E_i = -q\psi$  and  $E_F - E_i = -q\phi_n$ , so,  $n$  becomes  $\phi_n$  and  $p$  become  $\phi_p$ . So, this basically get reverse.

So, this is  $E_i$  is basically  $E_i$  the internal potential, is same as the potential. So, if you look at the band diagram of let us say p n junction, if you recall the p n junction, so, this is p type. So, in p type, the Fermi level is somewhere here and in n type Fermi level is close to the conduction vent. So, this is your  $E_F$ . Now, here  $E_F n = E_F p$  in equilibrium. And then if you look at the internal potential which is  $E_i$  so, this is  $E_i$ .

Now, for  $n$ ,  $n = n_i \exp(E_F - E_i)$  so, this difference. So, this is basically your  $q$  times  $V$ . And here, if you see this is  $E_i - E_F$  so, for a p type, it is  $E_i - E_F$  so that is  $\phi_p - \phi_n$ . So, if you see here,  $E_F$  is below  $E_i$  is above so, this will be  $-q$  times  $V$  the energy. So, you see here, for p type or for the whole concentration exponential  $-V$  by  $V_T$  for electron it is exponential  $V$  by  $V_T$ .

So,  $V$  is as far as the band diagram is concerned, is the difference between the Fermi level and the intrinsic level, so that difference is  $q$  times  $V$  so, applied potential. So, if you apply a potential here and let us say this potential is 0 then potential is 0 here, potential is 0 here. Now, what is happening? So, on the p sat on the n the inside, so, your  $E_i$  is above  $E_F$  is now you notice here that  $E_F$  is aligned with the potential throughout the  $E_F$  is 0.

But then how the potential is changing inside this device? So, you can see here  $E_i$  is above. So that means there is some positive potential and here  $E_i$  is below so, this energy is  $-qV$ . So, there is negative potential energy here. Now, if you will plot their band diagram, the potential diagram, so that energy is increasing. So that means potential is decreasing. So, potential will increase like this, so, this will be 0, this will be  $V$ .

So that potential is increasing. But if you see here it is 0 potential, it is 0 potential here. So, how do we understand this thing? That inside the potential is increasing when you go from p to n side but outside that the terminals this is also 0 potential, this is also 0 potential. So that has to be understood in terms of the intrinsic energy level. So, this is aligned with the Fermi level. So, this side, intrinsic energy level is up you see.

Here intrinsic energy level is down so, here basically, what you see? You see some positive energy. So, positive energy means that means different colour here positive energy means the potential is down here. So, this is your 0 potential inside there is a potential change and that is the difference between  $E_i - E_f$ . So, this is  $E_i - E_f$  by  $q$ . And here also, this is also  $E_i - E_f$  by  $q$ .

So, here  $E_i - E_f$  by  $q$  is positive and here  $E_i - E_f$  by  $q$  is negative. So that means potential is up here potential is down here. So, what it does see here? Potential goes inside it sees a jump here then inside it actually increases and at this boundary **(0) (08:03)** here and this 0 so, potential is like this basically. This is how the potential diagram inside the p n junction will look like. So, at this terminal potential 0 and at this terminal potential is 0.

So now, you notice here there are three built-in potentials. One is at the p n meteorological junction that is  $V_{bi}$  then at the this contact and p type region, this potential which is negative and then at the N type and the contact and this is positive potential here. So, what is the value? If you take it is  $E_i - E_f$  so, this will be  $kT$  by  $q \log$  of  $p$  by  $n_i$ . Because this is so, p type, so, whole is large but this is negative, so, this  $-kT$  by  $q \log p$  by  $n_i$  here it is positive.

So, the potential is  $kT$  by  $q \log$  of here see that difference  $E_f - E_i$  which is  $n$  by  $n_i$ . So, this can also be written as  $kT$  by  $q \log$  of  $n$  by  $n_i$ . Because here  $n$  is  $n_i^2$  by  $n_i$  or  $p$  so, this both are same basically. So, the potential with respect to the contact and the semiconductor is

kT by q log of n by n i. So, if electrons are more than the potential inside is more or that means the energy is actually low.

So, this basically explains that with respect to the boundary condition, how the potential is varying inside a piece of semiconductor? So, once we understood this point here. Now, we can discretize this Poisson equation.

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## LINEARIZATION OF POISSON EQUATION

Poisson equation

$$\frac{d^2\psi}{dx^2} = -\frac{\rho}{\epsilon} = -\frac{q}{\epsilon}(p-n+N_D^+-N_A^-)$$

$\frac{\partial^2\psi}{\partial x^2} = \frac{\partial^2\psi}{\partial x^2}$

$$\lambda^2 \cdot \left( \frac{\psi_{i+1,j} - \psi_{i,j}}{h_i} - \frac{\psi_{i,j} - \psi_{i-1,j}}{h_{i-1}} + \frac{\psi_{i,j+1} - \psi_{i,j}}{k_j} - \frac{\psi_{i,j} - \psi_{i,j-1}}{k_{j-1}} \right) - n_{i,j} + p_{i,j} + C_{i,j} = 0$$

$\frac{\partial^2\psi}{\partial x^2} = \frac{\psi_{i+1} - 2\psi_i + \psi_{i-1}}{h^2}$

- Finite difference discretization:
  - Potential varies linearly between mesh points
  - Electric field is constant between mesh points
- Linearization → Diagonally-dominant coefficient matrix A is obtained

$\frac{\partial^2\psi}{\partial x^2} = \frac{\psi_{i+1} - 2\psi_i + \psi_{i-1}}{h^2}$

$\frac{\partial^2\psi}{\partial x^2} = \frac{\psi_{i+1} - 2\psi_i + \psi_{i-1}}{h^2}$

$A\psi = b$

$\psi \rightarrow \psi_i$   
 $p \rightarrow p_i$   
 $n \rightarrow n_i$   
 $C \rightarrow C_i$

SEMICONDUCTOR DEVICE MODELING AND SIMULATION

So, this we have already seen that  $d^2\psi/dx^2$  is now, this is I have written for 1 dimension but for 2 dimension it will be  $d^2\psi/dx^2 + d^2\psi/dy^2$ . Now,  $d^2\psi/dx^2$ , we wrote that  $d^2\psi/dx^2$  is  $\psi$  at point  $i$ ,  $\psi_{i+1} - 2\psi_i + \psi_{i-1}$  divided by  $2\Delta x^2$ . Now, here it is shown for non uniform grid. So, this can also be written as  $d^2\psi/dx^2$ .

So, can also be written as  $d\psi/dx - d\psi/dx$  at 2 neighbouring points, so, this is at let us says we take at  $i+1$  and we take at  $i$  and divide by your the gap between the 2 basically. So, if you consider these two points here, let us say this is  $i$  this is  $i+1$ . This is  $i-1$  so,  $\psi_{i+1}$  the derivative, so,  $i+1 - i$  divided by  $\Delta x$  then  $\psi_i$  derivative,  $i - i - 1$  divided by  $h_{i-1}$ . So, this is simply, you can identify. What is this one?

This is forward difference, this is also forward difference. Then we are taking the derivative at  $i+1$  and  $i$ . Then this is the difference basically. So, what we do here? Because this distance and this distance, so, this we call  $h_i$  this we call  $h_{i-1}$ . So, we are basically having

derivative in these two regions, so, we are dividing this thing by the average of these two because we have taken the double derivative here at middle point.

So, divide by this average of  $h_i + h_{i-1}$  by 2 so, this can also be done but if you consider that  $h_i = h_{i-1}$ . What you will get? This  $h_i$  into  $h_{i-1}$  so, this will become  $h_i$  so, this is  $h_i$  by 2 so,  $2 h_i$  by 2 becomes  $h_i$  square. So, this is basically  $\psi_{i+1} - 2\psi_i + \psi_{i-1}$  divided by  $h$  square, so, actually  $\Delta h$  square. So, for uniform grid you will have just  $h$  square at the in the denominator.

Similarly, for  $y$  derivative along  $y$  so, this is  $d^2 \psi$  by  $dx$  square then this is right side we can take to other side that is  $-q$  by  $\psi$  becomes positive here. So,  $+q$  by  $\psi$ ,  $p - n + + N D + - N A C$ . So, let us call it  $C$ . Now, you notice here if you, when you are going to solve the equation, the change in potential is order of few volt. So, your  $\psi$  is order of few volts. Then you have this  $n$  and  $p$  which is order of  $10$  is to power  $17$ ,  $18$  and so on.

And then again  $C$  is also of same order  $10$  is to power  $17$  or  $16$  the doping. You notice here this is few volt this is  $10$  is to power  $17$ . So, the difference is quite big. So, when you try will make the matrix to solve this, you will get  $A \psi = b$ . This will be very much is skewed. That means you will have number some number visually small and then there will be some number  $10$  is to power  $17$ .

So, it will be difficult to solve this kind of equation. So, what is done here? We linearize it and we scale it. So, there is a process called scaling and then linearizing it. So, linearizing is done through the writing these difference equations and converting to algebraic equation. And scaling is so that we make it the values are such that they are of the same order. So, how do we scale it? What we do? We can take  $q$  by  $\epsilon$  from here.

And this is of course constant if  $\epsilon$  is constant, this can be taken out and it can be merged with some constant. Then instead of writing  $\psi$  we write this equation in terms of scaled potential. So, we scale  $\psi$  with some scaling potential then  $p$  with some value. Let us say you can scale with  $n_i$  and so on.  $N$  can also be scaled with  $n_i$  and position  $x$  can also be scaled with respect to debye length. So that we have done.

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SCALING FACTORS			
Variable	Scaling Variable	Formula	
Space	Intrinsic Debye length ( $N = n_i$ ) Extrinsic Debye length ( $N = N_{max}$ )	$L_D = \sqrt{\frac{\epsilon k_B T}{qN}}$	
Potential	Thermal voltage	$V_T = k_B T / q$	
Carrier concentration	Intrinsic concentration Maximum doping concentration	$N = n_i$ $N = N_{max}$	
Diffusion coefficient	Practical unit Maximum diffusion coefficient	$D = 1 \text{ cm}^2/\text{s}$ $D = D_{max}$	
Mobility		$M = \frac{D}{V_T}$	
Generation-recombination		$R = \frac{D N}{L_D^2}$	
Time		$T = \frac{L_D^2}{D}$	

*Handwritten notes:*  
 Modified variables:  $\tilde{\psi} = \frac{q\psi}{k_B T}$ ,  $\tilde{n} = \frac{n}{n_i}$ ,  $\tilde{p} = \frac{p}{n_i}$ ,  $\tilde{D} = \frac{D}{D_{max}}$ ,  $\tilde{t} = \frac{t}{T}$   
 Continuity eq:  $\frac{dn}{dt} = \frac{1}{q} \frac{dJ_n}{dx} + G - R$   
 Poisson eq:  $\frac{d^2\psi}{dx^2} = -\frac{\rho}{\epsilon} = -\frac{q}{\epsilon} (p - n + N_D^+ - N_A^-)$   
 Currents:  $J_n = qn\mu_n E + qD_n \frac{dn}{dx}$ ,  $J_p = qp\mu_p E - qD_p \frac{dp}{dx}$   
 Mobility:  $\mu = \frac{D}{V_T}$   
 Generation-recombination:  $R = \frac{D N}{L_D^2}$   
 Time:  $T = \frac{L_D^2}{D}$   
 Scaling:  $\tilde{\psi} = \frac{q\psi}{k_B T}$ ,  $\tilde{n} = \frac{n}{n_i}$ ,  $\tilde{p} = \frac{p}{n_i}$ ,  $\tilde{D} = \frac{D}{D_{max}}$ ,  $\tilde{t} = \frac{t}{T}$   
 Poisson eq scaling:  $\frac{d^2\tilde{\psi}}{d\tilde{x}^2} = -\frac{q}{\epsilon} (n_i \tilde{p} - n_i \tilde{n} + N_D^+ - N_A^-)$   
 Continuity eq scaling:  $\frac{d\tilde{n}}{d\tilde{t}} = \frac{1}{q} \frac{d\tilde{J}_n}{d\tilde{x}} + G - R$

So, these are the different scaling things. Now, let us apply this to Poisson equation  $\frac{d^2 \psi}{dx^2} = -\frac{\rho}{\epsilon}$ . So, here, if you write  $\frac{d^2 \psi}{dx^2}$ , so,  $\frac{d^2 \psi}{dx^2}$  we have to scale the potential is to scale with  $V_T$ . So, what we can do?  $V$  can divide by  $V_T$  and  $V$  can multiply by  $V_T$  then  $dx^2$ . Now,  $dx^2$ , it will be divided by length and the length will be your space there is a debye length.

So, you can divide by  $L_D$  and you can multiply by  $L_D$  for this  $x^2$ . So, to  $L_D^2$  square by  $L_D^2$  square then is equal to  $-\frac{q}{\epsilon}$ . Now, you have  $p$  so,  $p$  can be scaled by intrinsic carrier concentration or the doping level. So, there are two ways basically, you can scale with  $n_i$  or you can scale with the **(0) (16:32)** scale with  $n_i$ . So,  $p$  by  $n_i$  then multiply by  $n_i$  then  $-n$  by  $n_i$  and multiply by  $n_i$  then  $+N_D + -N_A -$  divided by  $n_i$  and multiply by  $n_i$ .

Now, what we do?  $V_T$  by  $L_D^2$  square and  $n_i$  times  $q$  by  $\epsilon$ , we can put them together. So,  $V_T$  times  $n_i \epsilon$  by  $q L_D^2$  square, so, this becomes your  $\lambda$ . So now, you have all these are scaled variables. So, we can write  $\frac{d^2 \psi}{dx^2}$  let us say  $\tilde{\psi}$  by  $d\tilde{x}^2$  square is equal to or if you take the right left side that becomes  $\tilde{p}$ , so,  $p$  by  $n_i$  is  $\tilde{p}$  and this is your  $\lambda^2$  or  $\lambda$  whatever this if it is  $\lambda^2$ .

Then  $-\tilde{n} +$  this we call  $C$  so, this is  $C$ , so, we are basically solving in terms of  $\tilde{\psi}$ . Now, all these  $\tilde{x}$ ,  $\tilde{p}$ ,  $\tilde{n}$ ,  $C$  these are scaled values. Now, if you see the change, this  $\psi$  will change let us say if your scaling volt is 26 millivolt and you have a range between some 0 to 5 volt. So, it will be some 0 to 5 by 26 millivolt. So, better than of 0 to

100 then  $p$ , let us say it is 10 is to power varying from 10 is to power 16, 15, 17 to 10 is to power 10.

So now, instead of varying having the variation of 10 is to power 17. Now, the variation is over order of 10 is to power 6 or 7. And this is of course and if you reduce the variation then you can scale instead of  $n_i$  we can scale with some maximum doping also that can be done. But then you have to select whether you are dealing with the multi carriers. So, if you have to consider multi carriers, it is better to scale with respect to  $n_i$ .

And if you are not dealing with multi carrier, it is better to scale with respect to the maximum doping. So that the idea is that the variation should be small and then the whatever algebraic question we wrote, we can write this algebraic equation for this modified variables. So, what we do through the scaling? We get modified variables. Similarly, for current density  $J$  is  $q$  and  $\mu$  time  $C$ .

So,  $n$  will be scaled and  $\mu D$  here  $n$  you can be scaled and electric field. So, potential can be scaled, so, the electric field will also be scaled according to the potential and the space. So, this is for the space and then for potential is the thermal voltage at room temperature is around 26 millivolt then carrier concentration with respect to  $n_i$  or the maximum doping.

Diffusion coefficient usually scaled with respect to one or it can also be scaled with respect to the maximum value that is in the device that mobility. Mobility we know that  $D$  by  $\mu$  is  $kT$  by  $E$  so that is  $V_T$ . So, if  $D$  is 1 then  $M$  will be 1 by  $V_T$  if  $D$  is  $D_{max}$  then  $M$  by  $D_{max}$  by  $V_T$ . So, accordingly, the mobility will also be scaled and then generation recombination is a recombination rate, so that is related to the  $\tau$ .

So, you remember  $D$  is a diffusion coefficient  $n$  is the carrier concentration divided by length square. So that is basically because this diffusion length is equal to root of  $D \tau$ , so, diffusion length square is equal to  $D \tau$ , so,  $\tau$  is  $L^2$  by  $D$ . So, this is what done here  $L^2$  by  $D$ . So, 1 by  $\tau$  and then generation recombination is basically is proportional to  $n$  by  $\tau$ . So, it is scale with respect to  $D N$  by  $L^2 D$  square.

Then time of course  $L^2 D$  square with respect this  $\tau$ . So, this is  $L^2 D$  square by  $D$ . So, all these points are covered. A space potential carrier, concentration, mobility, time generation,



recombination, all these are scaled. And instead of using the original variables scaled variables are used. So, here the range is basically, the range of variation of these parameters is actually reduce.

So, instead of  $J_n$  you will have some  $\tilde{J}_n$  the modified current density and here also. So, these are is used in the continuity equation.

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The slide is titled "NUMERICAL SCHEME" and contains the following content:

- Linearization of the Poisson equation
- Scharfetter-Gummel Discretization of the Continuity equation
- scaling of variables (De Mari)
- Discretization of the equations
  - Finite Difference – easier to implement but requires more node points, difficult to deal with curved interfaces
  - Finite Elements – standard, smaller number of node points, resolves curved surfaces
  - Finite Volume

The slide also features a diagram of a mesh of irregular shapes and a small inset image of a man speaking.

Now, numerical scheme so, once we scale and linearize then we use a discretization. So, for Poisson equation the discretization is normal finite difference, discretization and that is with respect to the potential. And scaling of the variable is attributed to De Mari a scientist introduce this technique. Then of course, this discretization that we have discussed, is at some level basically. Because there are different methods of discretizing it.

So, the different ways of discretizing so, it could be finite difference that we have discussed it could be finite element. So, in finite element, what is done? Instead of taking a point some elements are chosen basically. And here you can have more irregular geometries. So, this some triangles are formed and around that triangle you actually do the through variational approach.

You integrate this region and modify the equation accordingly. So, this is a finite element which is good for non standard geometries or curved geometries but and it has a small number of node points and it can easily resolve the curved surfaces. Then there are other method like finite volume then there are other spectral methods are also there. Boundary

element, matters are there. So, there are different methods to discretize and solve these equations.

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**CREDIT TO SCHARFETTER-GUMMEL**

Current equation:  $J_{i+1/2}^n = en\mu_{i+1/2}^n E_{i+1/2} + eD_{i+1/2}^n \frac{dn}{dx}$

Boundary conditions:  $n(\Psi_i) = n_i$ ,  $n(\Psi_{i+1}) = n_{i+1}$

Handwritten notes include:  $\frac{dn}{dx} = \frac{dn}{d\Psi} \frac{d\Psi}{dx} = \frac{dn}{d\Psi} \frac{\Psi_{i+1} - \Psi_i}{\Delta x}$ ,  $n_i = C e^{\Psi_i/V_T}$ ,  $n_{i+1} = C e^{\Psi_{i+1}/V_T}$ , and  $\frac{dn}{d\Psi} = \frac{n}{V_T}$ .

Now, the continuity equation this is attributed to Scharfetter Gummel scientist to introduce this method, what happens? If you consider simple, let us say this is your grid point. Now, if you discretize along this grid point. So, let us say we are discrete as in the potential. So, when we discretize potential, we make some assumption that potential is linearly varying. Then we will also discretize this for carrier concentration.

So, if we discretize and then we say that carrier concentration is linearly varying which will not be correct. Because your carrier concentration is proportional to exponential psi by V T so, it is a exponential function. So that means, if your psi linearly varying the potential is linearly varying across grid point then your carrier concentration cannot vary linearly. It has to vary exponentially.

So, in this method what is done for the carrier concentration? A different technique is used. So, let us look how it is done basically? Now, let us look at the current equation. This is the equation for current and we look at the continuity equation This is the continuity equation is  $dn/dt = \text{div} \cdot J_n + G - R$ . So, in case of steady state  $dn/dt$  will be 0. So, this continuity equation will reduce to  $\text{div} \cdot J_n = G - R$  with some sign.

So, this will be your continuity equation. So, continuity equation basically uses the current density equation. Now, you look at the current density equation, so, what is done here? These are the grid points. So, you cannot define current at 1 node. The current has to flow between the nodes. So, let us consider  $i$  and this is  $i + 1$ . So, what is the current between these two nodes?

So, what we do actually? We take the middle where there is no node and let us call it  $i + \text{half}$ . So,  $J$  between node  $i$  and  $i + 1$  is written as  $J$  at  $i + \text{half}$  now we know that  $J = n e \mu$ , so,  $n E \mu$  times electric field +  $e$  times  $D$  times  $dn$  by  $dx$ . Now, this all has to be evaluated at  $i$  and half so,  $n$  also need to evaluate at  $i + \text{half}$ .  $E$  is constant  $\mu$  also need to evaluate at  $i + \text{half}$   $E$  also at  $i$  and half electric field  $D$  also at  $i + \text{half}$  and this  $n$  also at  $i$  and half.

Now, since we cannot use that  $n_i$  and  $n_{i + 1}$  so, this we cannot write that in the middle, this will be  $n_i + n_{i + 1}$  by 2. So, this we cannot write because your current, the carrier concentration vary exponentially with respect to potential. So, it does not vary linearly between two node points. Of course, if you take node points very small, even then the variation can be significant and there may be convergence issues.

So, the another possibility is to make the spacing very small but that will be impractical and lot of grid points will come into the picture. So now, what we do? Instead of discretizing the  $n$  we discretize only the potential  $\psi$ . So, we can rearrange this equation and from this we can get  $dn$  by  $dx$  and we express in terms of current. Now, current can be assumed constant between these two nodes.

So, your  $dn$  by  $dx$  is you divide by  $e D$  so,  $n \mu e$  by  $e D$  so,  $e$  cancel out, is equal to  $J$  by  $e D$ . So, this equation directly coming from the current density equation. Now,  $dn$  by  $d\psi$  we are not discretizing  $n$  with respect to  $x$ . So, we write  $dn$  by  $dx$  as  $dn$  by  $d\psi$  times  $d\psi$  by  $dx$ . So,  $n$  is a function of potential  $\psi$  and then this is  $d\psi$  by  $dx$ . Now,  $\psi$  we assume is linearly varying.

So, if  $\psi$  is linearly varying then  $\psi$  by  $dx$  can be written as  $\psi_{i + 1} - \psi_i$  by  $\Delta x$  +  $m$  so, this will be times  $dn$  by  $d\psi$ . Now, we substitute this into the equation here, so, we can write  $dn$  by  $d\psi$  and we divide by this term here. So, let me write here  $dn$  by  $d\psi$ , this +  $n \mu E$  by  $D$  times  $\psi_{i + 1} - \psi_i$  by  $\Delta x = J$  by  $e D$  times  $i, i + 1 - \psi_i$  by  $\Delta x$ . Now,

this  $E$  and  $d\psi$  are same with a sign, so, we will write a minus sign here and cancel these two.

So,  $d\psi$  is  $V T$ , so, this can be written as  $d\psi = n$  by  $V T$  because  $d\psi$  is  $V T = J$  by  $E D$  times  $\Delta x$  by  $\psi_{i+1} - \psi_i$ . So, this is the written equation written here. Now, if you look at this equation, this is a linear equation. So, if you recall this in mathematics,  $dy/dx = a - b$ . So, what is the solution for this equation?  $Y = e$  to the power  $ax + b$  by  $a$ . So, some coefficient times  $e$  to the power  $ax + b$  by  $a$ .

And then so, here also you can write for the  $n$ . So, your  $n$  can be written, as  $n$  is equal to some coefficient times  $e$  to the power  $ax$ . Now,  $a$  is  $1$  by  $V T$ , so, it can be written as  $\psi$  by  $V T$  then  $+ b$  by  $a$  so, this is let us say  $b$ . So, let us say,  $b$  by  $a$ . Now, this is subjected to two boundary conditions. So,  $n$  at point  $i$  will be exponential  $\psi_i$  by  $V T$  and  $n$  at  $i + 1$  will be  $c$  times  $e$  to the power  $\psi_{i+1}$  by  $V T + b$  by  $a$ .

So, from this you can get  $c$ ,  $c$  will be you take the difference  $n_{i+1} - n_i$  divided by  $e$  to the power  $\psi_{i+1}$  by  $V T - e$  to the power  $\psi_i$  by  $V T$ . So, this will be coefficient and then you substitute back here, so, your  $n$  will be this  $C$  here times  $e$  to the power  $\psi$  by  $V T + b$  by  $a$ . Now,  $b$  by  $a$  is this  $J$  by  $E D$  times  $\psi$  by  $V T$  so, this we already know. Now, if you notice here, it will have some coefficient of  $n_{i+1}$ .

It will have some coefficient of  $n_i$  so,  $n_{i+1}$  will have  $e$  to the power  $\psi$  by  $V T$  by denominator and this will have some also  $-e$  to the power  $\psi$  by  $V T$  and then this denominator here. This domain can be multiplied by  $e$  to the power  $\psi$  by  $\psi_i$  by  $V T$ .

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**CONTINUITY EQUATION**

$$\frac{dn}{d\Psi} \frac{d\Psi}{V_i} = \frac{\Delta}{e(\Psi_{i+1} - \Psi_i)} \frac{J_{i+1/2}^n}{D_{i+1/2}^n}$$

Boundary conditions:  $n(\Psi_i) = n_i$     $n(\Psi_{i+1}) = n_{i+1}$

Therefore,  $n(\Psi) = n_i [1 - g(\Psi)] + n_{i+1} g(\Psi)$

$$J_{i+1/2}^n = en\mu_{i+1/2}^n E_{i+1/2} + eD_{i+1/2}^n \frac{dn}{dx}$$

$$J_{i+1/2}^n = \frac{eD_{i+1/2}^n}{\Delta} [n_{i+1} B(\frac{\Psi_{i+1} - \Psi_i}{V_i}) - n_i B(\frac{\Psi_i - \Psi_{i+1}}{V_i})]$$

$B(x) = \frac{x}{e^x - 1}$    Bernoulli fn

$g(\Psi) = \frac{e^{\frac{\Psi - \Psi_i}{V_i}} - 1}{e^{\frac{\Psi_{i+1} - \Psi_i}{V_i}} - 1}$

SEMICONDUCTOR DEVICE MODELING AND SIMULATION

So, what you will have basically? you will have basically this is  $n_i$  then this is  $n_{i+1}$   $e$  to the power  $\psi_i - \psi_i$  by  $V_T - 1$   $e$  to the power  $\psi_{i+1} - \psi_i$ ,  $i$  by  $V_T - 1$  and this is  $1 -$  this thing, so, this will be denominator will be same as this  $1$  and  $e$  to the power  $\psi_{i+1} - \psi_i$ ,  $i$  by  $V_T - a$  to the power  $\psi_i - \psi_i$  by  $V_T$ . So,  $e$  to the power  $\psi_i - \psi_i$  by  $V_T$  for  $n_{i+1}$  coefficient is positive for  $n_i$  the coefficient is negative that you can easily see here.

For  $n_{i+1}$  the population positive for  $n_i$  coefficient is negative. So, to write it compact we replace this function by  $g(\Psi)$  so, this is your  $g(\Psi)$ . So, your  $n$  is simply written as  $n_i [1 - g(\Psi)] + n_{i+1} g(\Psi)$ . Now, if you look at the  $g$  let us say  $g(\Psi)$ . So, if you see a reason here, let us say this is point  $i$  this is point  $i + 1$ . Now, the field is varying linearly, so, your  $\psi$  varying linearly but your  $n$  will vary exponentially.

So, if your  $\psi_i - \psi_i$  by  $V_T$  if it this is  $0$ , let us say  $\psi_i = \psi_{i+1}$  so that is, potential is  $0$ , so, there is no change. So that means your this will be linear, basically because this coefficient is  $0$  this coefficient is also  $0$ . So, your  $n$  will vary linear here if  $\psi_{i+1}$  is more than  $\psi_i$  so, it is plus a few  $10$  of  $V_T$  because let us say this is  $10$  times  $V_T$  so,  $\psi_i$  it is some  $10$ . So then it will increase actually exponentially.

So, your it will be something like this and as you increase it so, at higher voltage, it is actually have more slope basically. And if it is minus then it will basically look like this. So, this is  $-10$ , this is  $+10$ , so, this is how it is changing. So, your  $n$  is not changing linearly, so that is what you have done and when  $\psi$  is changing linearly. Then of course we can

substitute this  $n$  into the current density equation which has  $e n \mu$  times  $e + E$   $10$  times  $dn$  by  $dx$ .

Now, here you have  $n$  here you have  $dn$  by  $dx$ , so,  $n$  means this  $g \psi$  is there  $dn$  by  $dx$  means, if you take the derivative of  $g$  by  $dx$  or that will be  $dg$  by  $d\psi$  times  $d\psi$  by  $dx$ . So,  $dg$  by  $d\psi$  times  $d\psi$  by  $dx$  which is electric field, so, electric field has come here and  $\mu$  and  $d$  are related by  $V T$ . So,  $dg$  by  $d\psi$  you can find from here. This will be same denominator is same. It is not varying because  $\psi_i$  and  $\psi_{i+1}$  are the node values.

So, with respect to  $\psi$ , if you take, it will be  $1$  over  $V T$  times  $e$  to the power  $\psi - \psi_i$  by  $V T$  by this denominator. So, here you have  $e$  to the power this  $\psi_i - i V T$  and times  $1$  by  $V T$ . Then when you substitute and by it there is some algebra is there but you can do it so, by algebraic simplification.  $J_i$  for  $J_n$  can be represented as  $e D$  by  $\Delta x$  times  $n_{i+1}$  times a function called Bernoulli function which is  $B(x)$  is  $x$  by  $e$  to the power  $x - 1$ .

So, this will be basically  $\psi_{i+1} - \psi_i$  by  $V T$  divided by  $e$  to the power  $\psi_{i+1} - \psi_i$  by  $V T - 1$ . So, you see here for  $n$  you have  $g \psi$  for  $dn$  by  $dx$  you have this function. So, when you rearrange it basically, so, it will have some coefficient for positive for  $n_{i+1}$  and so,  $n_{i+1}$  has positive  $g \psi$   $n_i$  is  $-g \psi$  so, again this signs are followed here. And the current is expressed in terms of  $\psi$ , so, it is not in terms of  $n_{i+1} - n_i$  by  $\Delta x$ .

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## CONTINUITY EQUATION

- Electron and hole densities  $n$  and  $p$  vary exponentially between mesh points  
→ relaxes the requirement very small mesh sizes
- The exponential dependence of  $n$  and  $p$  upon the potential is buried in the Bernoulli functions

Continuity eqn

$$\frac{D_n^{i+1/2}}{\Delta^2} B\left(\frac{\Psi_{i+1} - \Psi_i}{V_T}\right) n_{i+1} - n_i \left[ \frac{D_n^{i+1/2}}{\Delta^2} B\left(\frac{\Psi_i - \Psi_{i-1}}{V_T}\right) + \frac{D_n^{i+1/2}}{\Delta^2} B\left(\frac{\Psi_i - \Psi_{i+1}}{V_T}\right) \right]$$

$$+ \frac{D_n^{i+1/2}}{\Delta^2} B\left(\frac{\Psi_{i+1} - \Psi_i}{V_T}\right) n_{i+1} = G_i - R_i$$

$0 = \frac{\partial n}{\partial t} = \frac{1}{2} \frac{\partial J}{\partial x} + G - R$

$\frac{\partial J}{\partial x} \text{ term}$

$$\frac{D_p^{i+1/2}}{\Delta^2} B\left(\frac{\Psi_i - \Psi_{i+1}}{V_T}\right) p_{i+1} - p_i \left[ \frac{D_p^{i+1/2}}{\Delta^2} B\left(\frac{\Psi_{i+1} - \Psi_i}{V_T}\right) + \frac{D_p^{i+1/2}}{\Delta^2} B\left(\frac{\Psi_{i+1} - \Psi_{i-1}}{V_T}\right) \right]$$

$$+ \frac{D_p^{i+1/2}}{\Delta^2} B\left(\frac{\Psi_i - \Psi_{i+1}}{V_T}\right) p_{i+1} = G_i - R_i$$

SEMICONDUCTOR DEVICE MODELING AND SIMULATION

It is in terms of  $\psi$  only and then this is the basically equation and then you substitute to this the continuity equation, so which is basically  $dn$  by  $dt$  and so on. So, if you see here this is

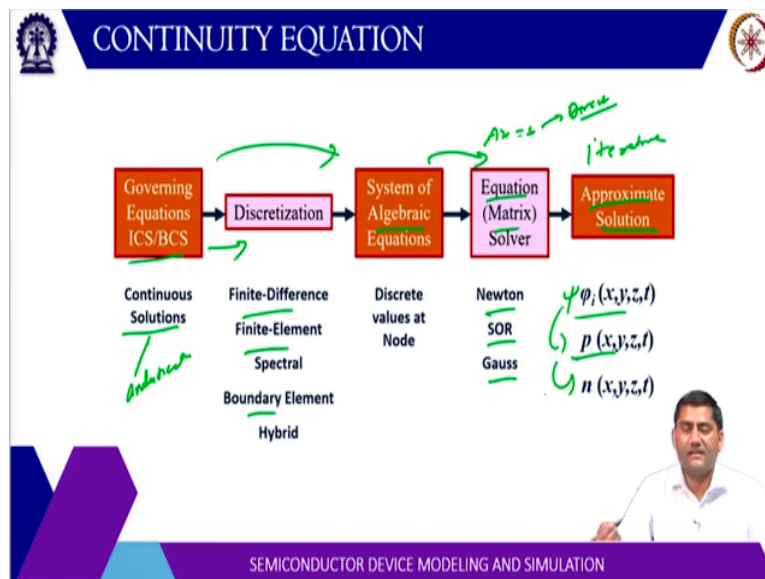
basically  $n_{i+1} - n_i$  and this is the coefficient of  $n_{i-1}$ . So, a double derivative of, if you see  $\frac{dn}{dt} = 1$  over  $q \frac{dJ}{dx} + \text{generation} - \text{recombination}$ . So, for steady state let us assuming state is a  $\frac{dn}{dt} = 0$ . So then this becomes 0.

So, this is  $\frac{dJ}{dx}$ . So, instead of writing in terms of  $n$  this  $J$  expression that we dragged here is used here, basically so,  $J$  of  $n + \frac{1}{2}$  and  $J$  of  $n - \frac{1}{2}$ . So, what is done here? See  $J$  of  $n + \frac{1}{2}$   $D_{i+\frac{1}{2}}$  times these Bernoulli functions. So,  $D_{i+\frac{1}{2}}$   $i - \frac{1}{2}$  and  $D_{i+\frac{1}{2}}$  times Bernoulli and this is  $d_{i+\frac{1}{2}}$  this is  $d_{i-\frac{1}{2}}$   $d_{i+\frac{1}{2}}$  and  $d_{i-\frac{1}{2}}$  is equal to net generation minus recombination.

Similarly, the expression is written for the wholes, also  $\frac{dJ}{dx} + \text{generation} - \text{recombination}$  is equal to 0. So, you get this kind of equation. Now, this is in you can write an  $x$ , you can write in  $y$  for 3-D also, you can also write it because more and more complicated. So, idea is that for the drift diffusion model when we discretize these governing equation, governing equations are the Poisson equation.

Then continuity equation and continuity equation is basically expressed in terms of the current density. So, we have to discretize the current density equation, using the Scharfetter Gummel method.

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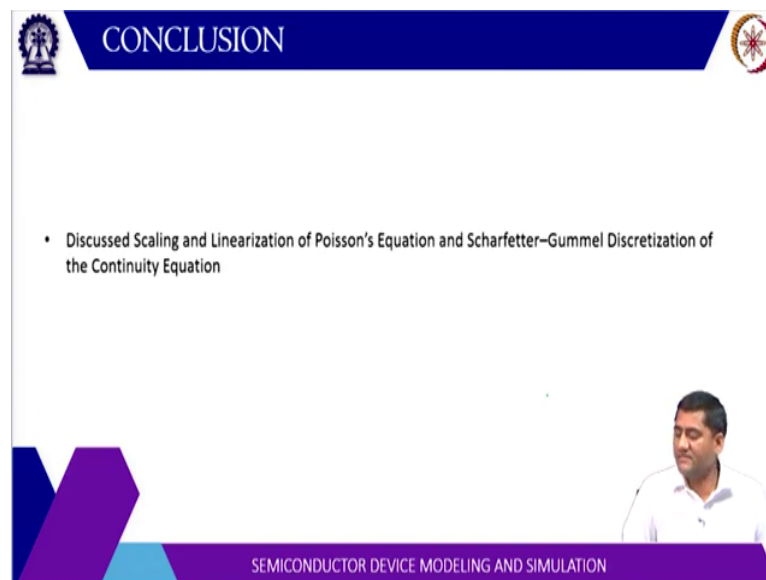
So, finally, what we do? So, this governing equations, of course, when solved analytically, we have continuous solution. So, where we discretize them so, using finite difference, finite element, boundary element and so on. Then what it does basically discretizing does it convert

the differential equation into algebraic equations. And then algebraic equation we get some  $Ax = b$ . So then of course, we have to solve for the matrix.

And there are different methods Newton method, successive over relaxation method, Gummel method, Gauss method and so on. And through iterative solutions, iterative solvers, we get the approximate solutions which are close enough to the accurate solution. And of course, if you directly solve it then you will get exact solution but direct method is difficult and it takes and impractical especially for the large size of the problems.

And then you get these variables the potentials, the psi and then from psi you can calculate the p and n.

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The slide features a dark blue header with the word "CONCLUSION" in white. On the left is a circular logo with a gear and a person, and on the right is a circular logo with a red and white star. The main content area is white and contains a single bullet point: "Discussed Scaling and Linearization of Poisson's Equation and Scharfetter-Gummel Discretization of the Continuity Equation". At the bottom, there is a purple and blue decorative graphic on the left and a video feed of a man in a white shirt on the right. The footer is a purple bar with the text "SEMICONDUCTOR DEVICE MODELING AND SIMULATION" in white.

So, in this lecture we have discussed the scaling and the linearization of Poisson equation and the Scharfetter Gummel method for the continuity equation. Thank you very much.